TOSHIBA 2SK2825

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

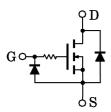
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FOR PORTABLE EQUIPMENT HIGH SPEED SWITCH APPLICATIONS ANALOG SWITCH APPLICATIONS

- High Input Impedance
- 1.5V Gate Drive
- Low Gate Threshold Voltage : $V_{th} = 0.5 \sim 1.0 \text{V}$
- Small Package

EQUIVALENT CIRCUIT

MARKING





This transistor is electrostatic sensitive device. Please handle with caution.

Unit in mm 1.6 ± 0.2 0.8 ± 0.1 +0.1 0.2-0.05 **GATE SOURCE** 3. DRAIN SSM **JEDEC EIAJ** TOSHIBA 2-2H1B

Weight: 2.4mg (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	$v_{ m DS}$	20	V
Gate-Source Voltage	v_{GSS}	10	V
DC Drain Current	$I_{\mathbf{D}}$	100	mA
Drain Power Dissipation	$P_{\mathbf{D}}$	100	mW
Channel Temperature	$\mathrm{T_{ch}}$	150	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	$^{\circ}\mathrm{C}$

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARAC	CTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage	Current	$I_{ m GSS}$	$V_{GS}=10V, V_{DS}=0$	_	_	1	μ A
Drain-Source I Voltage	Breakdown	V _(BR) DSS	$I_{D} = 100 \mu A, V_{GS} = 0$	20	_	_	v
Drain Cut-off	Current	$I_{ m DSS}$	$V_{DS}=20V, V_{GS}=0$	_	_	1	μ A
Gate Threshol	d Voltage	$ m v_{th}$	$V_{ m DS} = 1.5 V, \; I_{ m D} = 0.1 { m mA}$	0.5		1.0	V
Forward Trans	sfer Admittance	$ Y_{fs} $	V_{DS} =1.5V, I_{D} =10mA	35	70	_	mS
Drain-Source	ON Resistance 1	R _{DS} (ON)1	$I_D=1$ mA, $V_{GS}=1.2$ V	1	15	50	Ω
Drain-Source	ON Resistance 2	RDS (ON) 2	$I_D=10$ mA, $V_{GS}=1.5$ V	1	10	40	Ω
Drain-Source ON Resistance 3RDS (ON) 3		$I_D=10mA$, $V_{GS}=2.5V$		7	28	Ω	
Input Capacita	ance	$\mathrm{c}_{\mathrm{iss}}$	$V_{DS} = 1.5V, V_{GS} = 0, f = 1MHz$	-	12	_	pF
Reverse Transfer Capacitance C _{rss}		$V_{ m DS}\!=\!1.5 { m V}, V_{ m GS}\!=\!0, { m f}\!=\!1 { m MHz}$	_	3.4	_	pF	
Output Capacitance Coss		$V_{DS} = 1.5V, V_{GS} = 0, f = 1MHz$		12		pF	
Switching	Turn-on Time	ton	$V_{\rm DD} = 1.5 \text{V}, I_{\rm D} = 10 \text{mA},$	_	0.35	_	,,,
Time	Turn-off Time	${ m t_{off}}$	$V_{GS} = 0 \sim 1.5 V$	_	0.2	_	μ s

SWITCHING TIME TEST CIRCUIT



